

MITSUBISHI LSIs

M5M5V4R08J-12,-15

1997.11.20 Rev.F

4194304-BIT (524288-WORD BY 8-BIT) CMOS STATIC RAM

DESCRIPTION

The M5M5V4R08J is a family of 524288-word by 8-bit static RAMs, fabricated with the high performance CMOS silicon gate process and designed for high speed application.

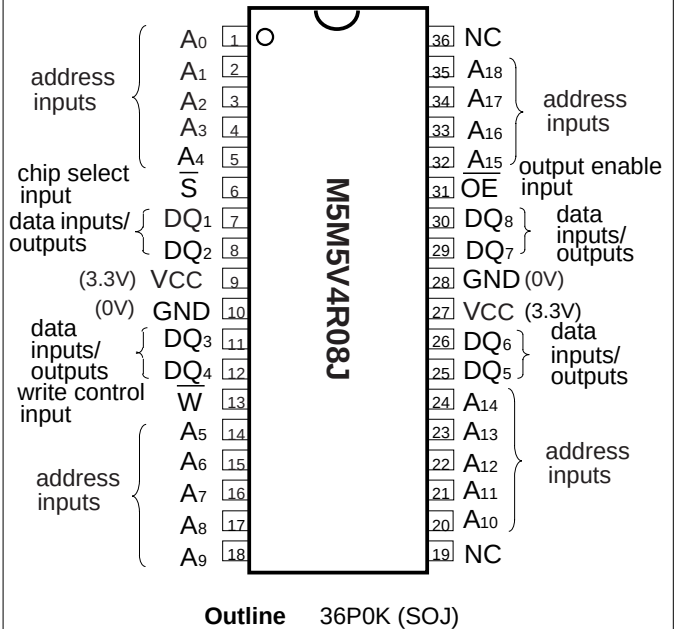
The M5M5V4R08J is offered in a 36-pin plastic small outline J-lead package(SOJ).

These device operate on a single 3.3V supply, and are directly TTL compatible. They include a power down feature as well.

FEATURES

- Fast access time M5M5V4R08J-12 12ns(max)
M5M5V4R08J-15 15ns(max)
- Low power dissipation Active 363mW(typ)
Stand by 3.3mW(typ)
- Single +3.3V power supply
- Fully static operation : No clocks, No refresh
- Common data I/O
- Easy memory expansion by $\bar{S}$
- Three-state outputs : OR-tie capability
- $\bar{OE}$ prevents data contention in the I/O bus
- Directly TTL compatible : All inputs and outputs

PIN CONFIGURATION (TOP VIEW)



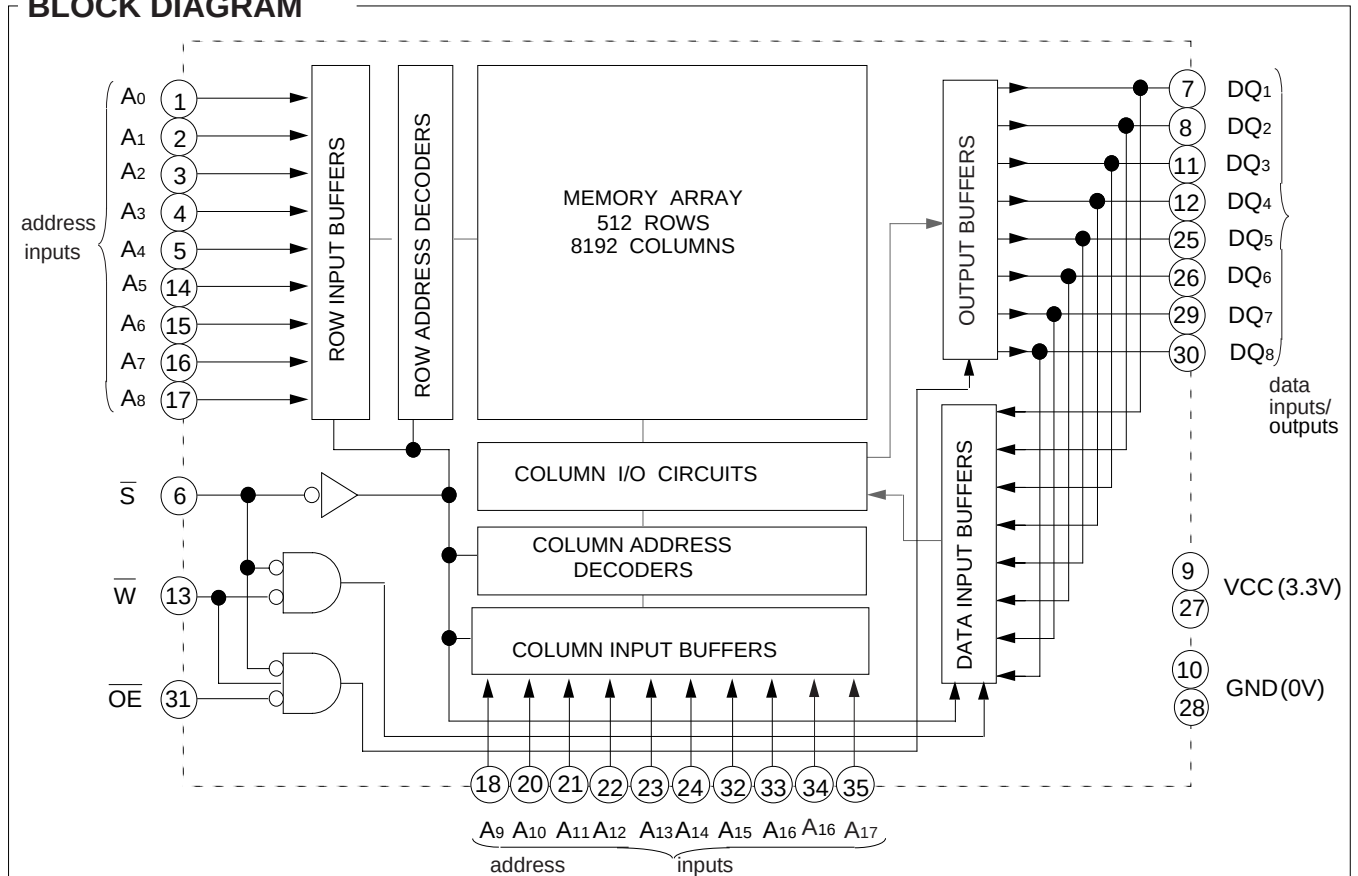
APPLICATION

High-speed memory units

PACKAGE

36pin 400mil SOJ

BLOCK DIAGRAM



FUNCTION

The operation mode of the M5M5V4R08J is determined by a combination of the device control inputs $\bar{S}$, $\bar{W}$ and $\bar{OE}$. Each mode is summarized in the function table.

A write cycle is executed whenever the low level $\bar{W}$ overlaps with the low level $\bar{S}$. The address must be set-up before the write cycle and must be stable during the entire cycle.

The data is latched into a cell on the trailing edge of $\bar{W}$ or $\bar{S}$, whichever occurs first, requiring the set-up and hold time relative to these edge to be maintained. The output enable input $\bar{OE}$ directly controls the output stage. Setting the $\bar{OE}$ at a high level, the output stage is in a high impedance state, and the data bus

contention problem in the write cycle is eliminated.

A read cycle is executed by setting $\bar{W}$ at a high level and $\bar{OE}$ at a low level while $\bar{S}$ are in an active state ($\bar{S}=\text{L}$).

When setting $\bar{S}$ at high level, the chip is in a non-selectable mode in which both reading and writing are disable. In this mode, the output stage is in a high-impedance state, allowing OR-tie with other chips and memory expansion by $\bar{S}$.

Signal- $\bar{S}$ controls the power-down feature. When $\bar{S}$ goes high, power dissipation is reduced extremely. The access time from $\bar{S}$ is equivalent to the address access time.

FUNCTION TABLE

$\bar{S}$	$\bar{W}$	$\bar{OE}$	Mode	DQ	Icc
H	X	X	Non selection	High-impedance	Stand by
L	L	X	Write	Din	Active
L	H	L	Read	Dout	Active
L	H	H		High-impedance	Active

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Conditions	Ratings	Unit
V _{cc}	Supply voltage	With respect to GND	-2.0* ~ 4.6	V
V _I	Input voltage		-2.0* ~ V _{CC} +0.5	V
V _O	Output voltage		-2.0* ~ V _{CC} +0.5	V
P _d	Power dissipation	T _a =25 °C	1000	mW
T _{opr}	Operating temperature		0 ~ 70	°C
T _{stg(bias)}	Storage temperature (bias)		-10 ~ 85	°C
T _{stg}	Storage temperature		-65 ~ 150	°C

*Pulse width ≤ 20ns, In case of DC:-0.5V

DC ELECTRICAL CHARACTERISTICS (T_a=0 ~ 70 °C, V_{cc}=3.3V ^{+10%}/_{-5%} unless otherwise noted)

Symbol	Parameter	Condition			Limits			Unit
					Min	Typ	Max	
V _{IH}	High-level input voltage				2.0		V _{CC} +0.3	V
V _{IL}	Low-level input voltage				-0.3		0.8	V
V _{OH}	High-level output voltage	I _{OH} = -4mA			2.4			V
V _{OL}	Low-level output voltage	I _{OL} = 8mA					0.4	V
I _I	Input current	V _I = 0~V _{CC}					2	μA
I _{OZ}	Output current in off-state	V _I ($\overline{S}$)= V _{IH} V _O = 0~V _{CC}					10	μA
I _{CC1}	Active supply current (TTL level)	V _I ($\overline{S}$)= V _{IL} other inputs V _{IH} or V _{IL} Output-open(duty 100%)	AC	12ns cycle			170	mA
				15ns cycle			160	
			DC				110	
I _{CC2}	Stand by current (TTL level)	V _I ($\overline{S}$)= V _{IH}	AC	12ns cycle			85	mA
				15ns cycle			80	
			DC					
I _{CC3}	Stand by current	V _I ($\overline{S}$)= V _{CC} ≥0.2V other inputs V _I ≤0.2V or V _I ≥V _{CC} -0.2V				1	10	mA

CAPACITANCE ($T_a=0 \sim 70^\circ\text{C}$, $V_{cc}=3.3\text{V}$ ^{+10%}/_{-5%} unless otherwise noted)

Symbol	Parameter	Test Condition	Limit			Unit
			Min	Typ	Max	
C _I	Input capacitance	$V_I = \text{GND}, V_I = 25\text{mVrms}, f=1\text{MHz}$			7	pF
C _O	Output capacitance	$V_O = \text{GND}, V_O = 25\text{mVrms}, f=1\text{MHz}$			8	pF

Note 1: Direction for current flowing into an IC is positive (no mark).

2: Typical value is $V_{cc}=5\text{V}, T_a=25^\circ\text{C}$

3: C_I, C_O are periodically sampled and are not 100% tested.

AC ELECTRICAL CHARACTERISTICS ($T_a=0 \sim 70^\circ\text{C}$, $V_{cc}=3.3\text{V}$ ^{+10%}/_{-5%} unless otherwise noted)

(1) MEASUREMENT CONDITION

Input pulse levels $V_{IH}=3.0\text{V}, V_{IL}=0.0\text{V}$

Input rise and fall time 3ns

Input timing reference levels $V_{IH}=1.5\text{V}, V_{IL}=1.5\text{V}$

Output timing reference levels $V_{OH}=1.5\text{V}, V_{OL}=1.5\text{V}$

Output loads Fig1 ,Fig2

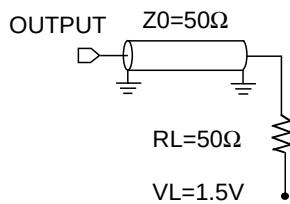


Fig.1 Output load

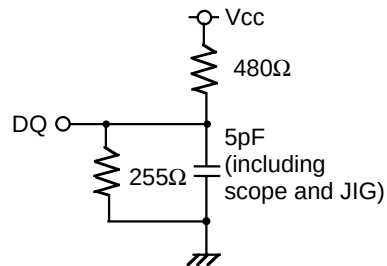


Fig.2 Output load for t_{en}, t_{dis}

(2)READ CYCLE

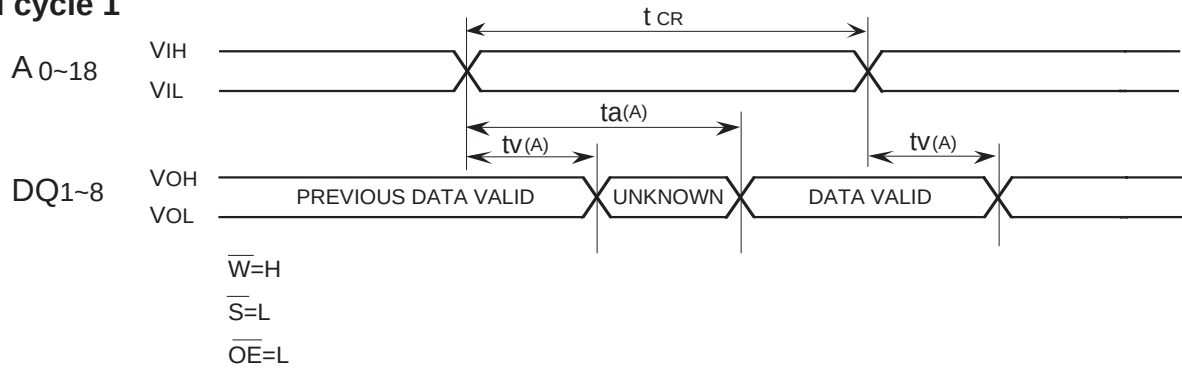
Symbol	Parameter	Limits				Unit
		M5M5V4R08J -12		M5M5V4R08J -15		
		Min	Max	Min	Max	
t _{CR}	Read cycle time	12		15		ns
t _{a(A)}	Address access time		12		15	ns
t _{a(S)}	Chip select access time		12		15	ns
t _{a(OE)}	Output enable access time		6		8	ns
t _{dis(S)}	Output disable time after $\overline{S}$ high	0	6	0	7	ns
t _{dis(OE)}	Output disable time after $\overline{OE}$ high	0	6	0	7	ns
t _{en(S)}	Output enable time after $\overline{S}$ low	0		0		ns
t _{en(OE)}	Output enable time after $\overline{OE}$ low	0		0		ns
t _{v(A)}	Data valid time after address change	3		3		ns
t _{PU}	Power-up time after chip selection	0		0		ns
t _{PD}	Power-down time after chip selection		12		15	ns

(3)WRITE CYCLE

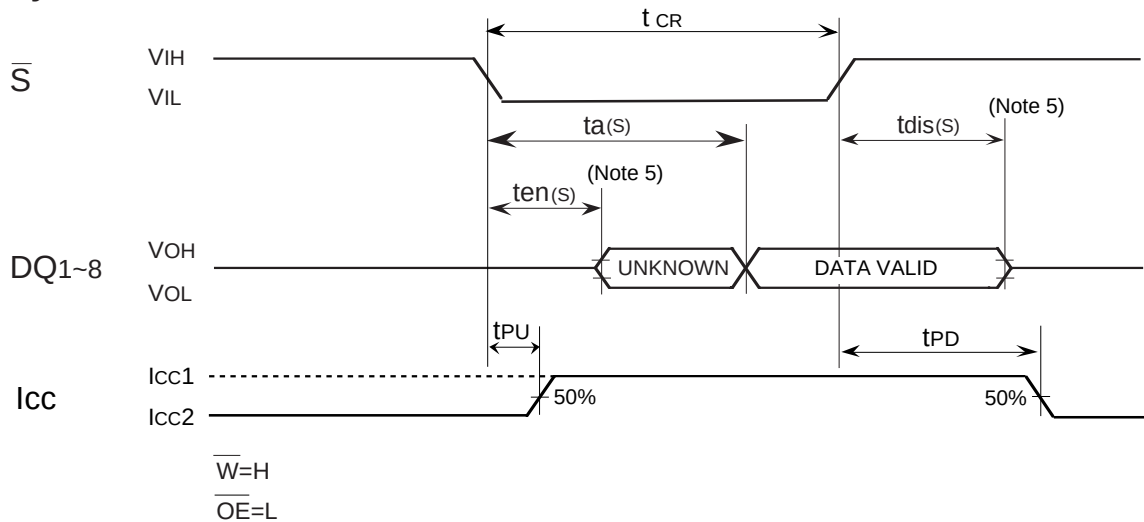
Symbol	Parameter	Limits				Unit
		M5M5V4R08J -12		M5M5V4R08J -15		
		Min	Max	Min	Max	
t _{CW}	Write cycle time	12		15		ns
t _{w(W)}	Write pulse width	10		12		ns
t _{su(A)1}	Address setup time($\overline{W}$)	0		0		ns
t _{su(A)2}	Address setup time($\overline{S}$)	0		0		ns
t _{su(S)}	Chip select setup time	10		12		ns
t _{su(D)}	Data setup time	6		7		ns
t _{h(D)}	Data hold time	0		0		ns
t _{rec(W)}	Write recovery time	1		1		ns
t _{dis(W)}	Output disable time after $\overline{W}$ low	0	6	0	7	ns
t _{dis(OE)}	Output disable time after $\overline{OE}$ high	0	6	0	7	ns
t _{en(W)}	Output enable time after $\overline{W}$ high	0		0		ns
t _{en(OE)}	Output enable time after $\overline{OE}$ low	0		0		ns
t _{su(A-WH)}	Address to $\overline{W}$ High	10		12		ns

(4)TIMING DIAGRAMS

Read cycle 1



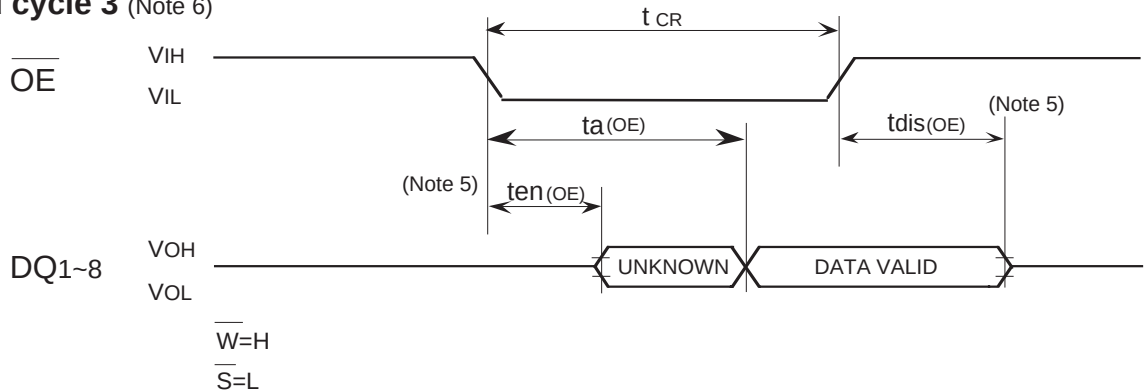
Read cycle 2 (Note 4)



Note 4. Addresses valid prior to or coincident with $\overline{S}$ transition low.

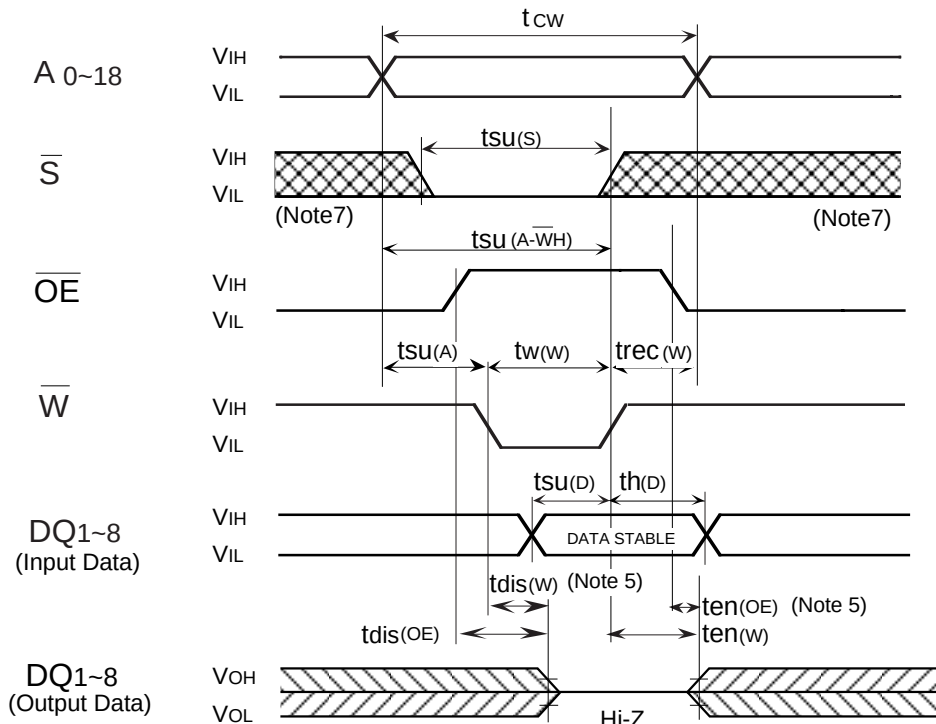
5. Transition is measured $\pm 500\text{mV}$ from steady state voltage with specified loading in Figure 2.

Read cycle 3 (Note 6)

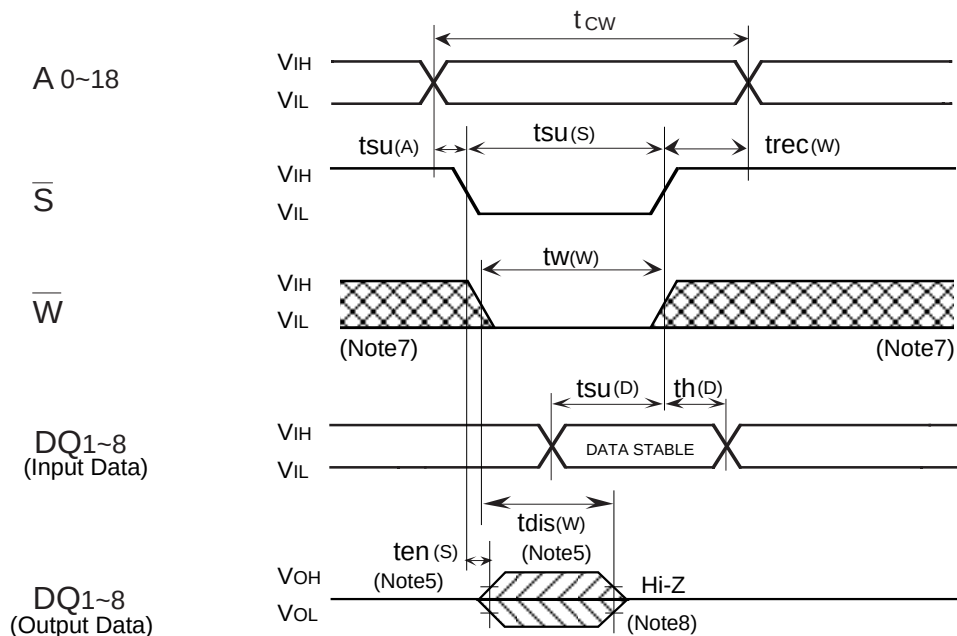


Note 6. Addresses and $\overline{S}$ valid prior to $\overline{OE}$ transition low by $(t_a(A)-t_a(OE))$, $(t_a(S)-t_a(OE))$

Write cycle ($\overline{W}$ control mode)



Write cycle ($\overline{S}$ control mode)



Note 7: Hatching indicates the state is don't care.

8: When the falling edge of $\overline{W}$ is simultaneous or prior to the falling edge of $\overline{S}$, the output is maintained in the high impedance.

9: t_{en} , t_{dis} are periodically sampled and are not 100% tested.